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21. (TWICE AMENDED) A MEMS formation method including:  
providing a SOI wafer including a single crystal silicon layer attached to an  
insulator layer;  
forming at least one first MEMS component by patterning the single crystal silicon  
layer;  
depositing at least one layer of polysilicon on the patterned single crystal silicon;  
and  
forming at least one second MEMS component by patterning the polysilicon.

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23. (AMENDED) The method of claim 21 wherein the at least one second MEMS  
component is a hinge.

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30. (TWICE AMENDED) A MEMS device comprising:  
at least one single crystal silicon component bonded to an insulator that rests on a  
handle wafer; and  
a polysilicon hinge derived from a layer of polysilicon applied over the at least one  
single crystalline component.